## ZXTP25140BFH 140V, SOT23, PNP medium power transistor

## Summary

$\mathrm{BV}_{\text {(BR)CEX }}>-180 \mathrm{~V}$; $\mathrm{BV}_{\text {(BR)CEO }}>-140 \mathrm{~V}$
$\mathrm{BV}_{\text {(BR)ECO }}>-7 \mathrm{~V}$;
$I_{C(\text { cont) })}=-1 \mathrm{~A}$
$R_{\text {ce(sat) }}=180 \mathrm{~m} \Omega$ typical

$V_{\text {ce(sat) }}<-260 \mathrm{mV}$ @ 1A ;
$\mathrm{P}_{\mathrm{D}}=1.25 \mathrm{~W}$

## Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

## Features

- High power dissipation SOT23 package

- 180 V forward blocking voltage
- Low saturation voltage


## Applications

- DC-DC converters
- High side switching


## Ordering information

| Device | Reel size <br> (inches) | Tape width | Quantity per <br> reel |
| :--- | :---: | :---: | :---: |
| ZXTP25140BFHTA | 7 | 8 mm | 3,000 |



Pinout - top view

## Device marking

## ZXTP25140BFH

## Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Collector-base voltage | $\mathrm{V}_{\text {CBO }}$ | -180 | V |
| Collector-emitter voltage (forward blocking) | $\mathrm{V}_{\text {CEX }}$ | -180 | V |
| Collector-emitter voltage | $\mathrm{V}_{\text {CEO }}$ | -140 | V |
| Emitter-collector voltage (reverse blocking) | $\mathrm{V}_{\text {ECO }}$ | -7 | V |
| Emitter-base voltage | $\mathrm{V}_{\text {EBO }}$ | -7 | V |
| Continuous collector current ${ }^{\text {(a) }}$ | $\mathrm{I}_{\mathrm{C}}$ | -1 | A |
| Peak pulse current | $\mathrm{I}_{\mathrm{CM}}$ | -3 | A |
| Power dissipation at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}^{\text {(a) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 0.73 | W |
| Linear derating factor |  | 5.84 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}^{\text {(b) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.05 | W |
| Linear derating factor |  | 8.4 | $\mathrm{~mW} /{ }^{\text {( }} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}^{\text {(c) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.25 | W |
| Linear derating factor |  |  |  |

## Thermal resistance

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Junction to ambient ${ }^{\text {(a) }}$ | $\mathrm{R}_{\text {ӨJA }}$ | 171 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{\text {(b) }}$ | $\mathrm{R}_{\text {ӨJA }}$ | 119 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{\text {(c) }}$ | $\mathrm{R}_{\text {ӨJA }}$ | 100 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{\text {(d) }}$ | $\mathrm{R}_{\text {ӨJA }}$ | 69 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## NOTES:

(a) For a device surface mounted on $15 \mathrm{~mm} \times 15 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with high coverage of single sided 10 c copper, in still air conditions.
(b) Mounted on $25 \mathrm{~mm} \times 25 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
(c) Mounted on $50 \mathrm{~mm} \times 50 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
(d) As (c) above measured at $\mathrm{t}<5 \mathrm{secs}$.

## ZXTP25140BFH

## Characteristics



## ZXTP25140BFH

## Electrical characteristics (at $\mathrm{T}_{\mathrm{AMB}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-base breakdown voltage | $\mathrm{BV}_{\text {CBO }}$ | -180 | -205 |  | V | $\mathrm{I}_{\mathrm{C}}=-100 \mu \mathrm{~A}$ |
| Collector-emitter breakdown voltage (forward blocking) | $\mathrm{BV}_{\text {CEX, }}$ | -180 | -205 |  | V | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-100 \mu \mathrm{~A} \\ & \mathrm{R}_{\mathrm{BE}} \leq 1 \mathrm{k} \Omega \text { or } \\ & -0.25 \mathrm{~V}<\mathrm{V}_{\mathrm{BE}}<1 \mathrm{~V} \end{aligned}$ |
| Collector-emitter breakdown voltage (base open) | $\mathrm{BV}_{\text {CEO }}$ | -140 | -160 |  | V | $\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}{ }^{(*)}$ |
| Emitter-collector breakdown voltage (reverse blocking) | $\mathrm{BV}_{\mathrm{ECO}}$ | -7 | -8.5 |  | V | $I_{E}=-100 u A^{(*)}$ |
| Emitter-base breakdown voltage | $\mathrm{BV}_{\text {EBO }}$ | -7 | -8.2 |  | V | $\mathrm{I}_{\mathrm{E}}=-100 \mu \mathrm{~A}$ |
| Collector cut-off current | $\mathrm{I}_{\text {CBO }}$ |  | <-1 | $\begin{aligned} & -50 \\ & -20 \end{aligned}$ | $\begin{aligned} & \mathrm{nA} \\ & \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{CB}}=-144 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CB}}=-144 \mathrm{~V}, \mathrm{~T}_{\mathrm{AMB}}=100^{\circ} \mathrm{C} \end{aligned}$ |
| Collector emitter cut-off current | $\mathrm{I}_{\text {CEX }}$ |  | - | -100 | nA | $\begin{aligned} & \mathrm{V}_{\mathrm{CE}}=-144 \mathrm{~V} ; \\ & \mathrm{R}_{\mathrm{BE}} \leq 1 \mathrm{k} \Omega \text { or } \\ & -0.25 \mathrm{~V}<\mathrm{V}_{\mathrm{BE}}<1 \mathrm{~V} \end{aligned}$ |
| Emitter cut-off current | $\mathrm{I}_{\text {EBO }}$ |  | <-1 | -50 | nA | $\mathrm{V}_{\mathrm{EB}}=-5.6 \mathrm{~V}$ |
| Collector-emitter saturation voltage | $\mathrm{V}_{\text {ce(sat) }}$ |  | $\begin{gathered} -40 \\ -110 \\ -90 \\ -170 \\ -180 \end{gathered}$ | $\begin{gathered} -50 \\ -135 \\ -110 \\ -230 \\ -260 \end{gathered}$ | mV <br> mV <br> mV <br> mV <br> mV | $\begin{aligned} & I_{C}=-0.1 A, I_{B}=-10 m A^{(*)} \\ & I_{C}=-0.1 A, I_{B}=-2 m A^{(*)} \\ & I_{C}=-0.5 A, I_{B}=-50 m A^{(*)} \\ & I_{C}=-0.5 A, I_{B}=-25 m A^{(*)} \\ & I_{C}=-1 A, I_{B}=-100 m A^{(*)} \end{aligned}$ |
| Base-emitter saturation voltage | $\mathrm{V}_{\text {be(sat) }}$ |  | -850 | -950 | mV | $I_{C}=-1 A, I_{B}=-100 m A^{(*)}$ |
| Base-emitter turn-on voltage | $\mathrm{V}_{\mathrm{BE} \text { (ON) }}$ |  | -800 | -900 | mV | $I_{C}=-1 A, V_{C E}=-2 V^{(*)}$ |
| Static forward current transfer ratio | $\mathrm{h}_{\mathrm{FE}}$ | $\begin{gathered} 100 \\ 100 \\ 20 \end{gathered}$ | $\begin{gathered} 200 \\ 190 \\ 30 \end{gathered}$ | 300 |  | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=-0.1 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V}^{(*)} \end{aligned}$ |
| Transition frequency | $\mathrm{f}_{\mathrm{T}}$ |  | 75 |  | MHz | $\begin{aligned} & I_{C}=-10 \mathrm{~mA}, V_{C E}=-20 \mathrm{~V} \\ & f=20 \mathrm{MHz} \end{aligned}$ |
| Output capacitance | $\mathrm{C}_{\text {OBO }}$ |  | 10 |  | pF | $\mathrm{V}_{\mathrm{CB}}=-20 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}{ }^{(*)}$ |
| Turn-on time | $\mathrm{t}_{\text {(on) }}$ |  | 102 |  | ns | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=-20 \mathrm{~V} . \mathrm{I}_{\mathrm{C}}=-100 \mathrm{~mA}, \\ & \mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=-10 \mathrm{~mA} \end{aligned}$ |
| Turn-off time | $\mathrm{t}_{\text {(off) }}$ |  | 854 |  | ns |  |

NOTES:
(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2 \%$.

## ZXTP25140BFH

## Typical characteristics



## ZXTP25140BFH

## Package outline - SOT23



| Dim. | Millimeters |  | Inches |  | Dim. | Millimeters |  | Inches |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Max. | Min. | Max. |  | Min. | Max. | Max. | Max. |
| A | 2.67 | 3.05 | 0.105 | 0.120 | H | 0.33 | 0.51 | 0.013 | 0.020 |
| B | 1.20 | 1.40 | 0.047 | 0.055 | K | 0.01 | 0.10 | 0.0004 | 0.004 |
| C | - | 1.10 | - | 0.043 | L | 2.10 | 2.50 | 0.083 | 0.0985 |
| D | 0.37 | 0.53 | 0.015 | 0.021 | M | 0.45 | 0.64 | 0.018 | 0.025 |
| F | 0.085 | 0.15 | 0.0034 | 0.0059 | N | 0.95 NOM |  | 0.0375 NOM |  |
| G | 1.90 NOM |  | 0.075 NOM |  | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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